

Silicon NPN Power Transistors

2SD437

DESCRIPTION

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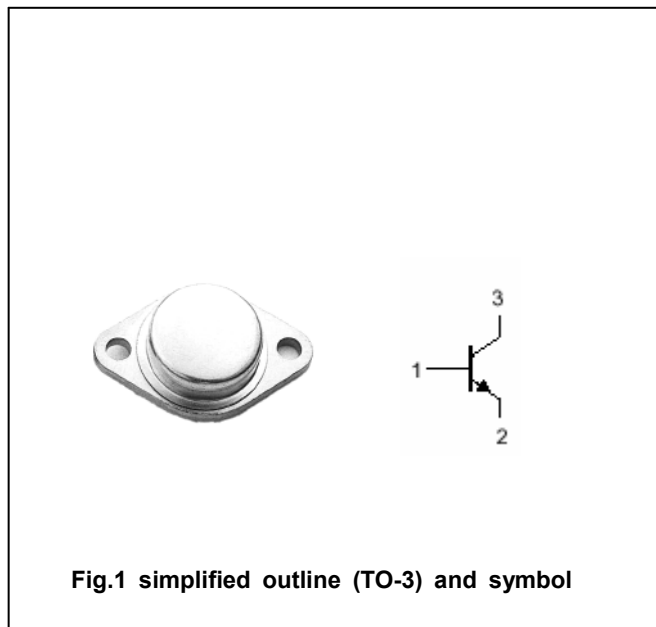
- With TO-3 package
- High voltage
- Fast switching speed

APPLICATIONS

- For switching regulator and power amplifier applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	350	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		15	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	80	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	350			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	6			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5 A; I _B =1 A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8 A; I _B =2.5 A			3.0	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =5 A; I _B =1 A			1.4	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =8 A; I _B =2.5 A			1.8	V
I _{CBO}	Collector cut-off current	V _{CB} =600V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15		50	
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =5V	10			

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PACKAGE OUTLINE

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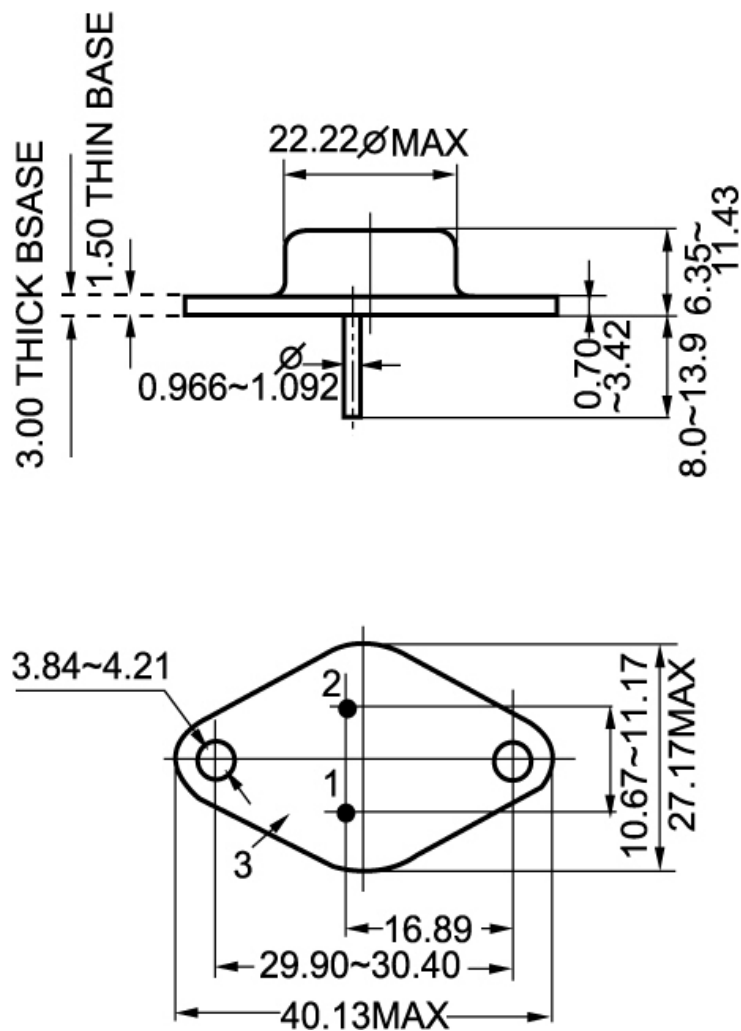


Fig.2 Outline dimensions